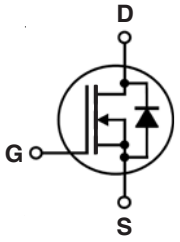
IXYS

Depletion Mode MOSFET

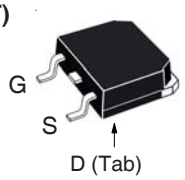
IXTT16N20D2
IXTH16N20D2

V_{DSX} = 200V
$I_{D(on)}$ ≥ 16A
$R_{DS(on)}$ ≤ 80mΩ

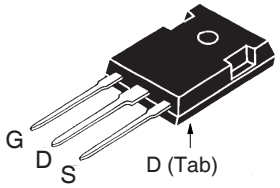
N-Channel



TO-268 (IXTT)



TO-247 (IXTH)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSX}	T_J = 25°C to 150°C	200	V
V_{DGX}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	200	V
V_{GSX}	Continuous	±20	V
V_{GSM}	Transient	±30	V
P_D	T_C = 25°C	695	W
T_J		- 55 ... +150	°C
T_{JM}		150	°C
T_{stg}		- 55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
M_d	Mounting Torque (TO-247)	1.13 / 10	Nm/lb.in.
Weight	TO-268	4	g
	TO-247	6	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSX}	V_{GS} = - 5V, I_D = 250μA	200			V
$V_{GS(off)}$	V_{DS} = 25V, I_D = 4mA	- 2.0		- 4.5	V
I_{GSX}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
$I_{DSX(off)}$	V_{DS} = V_{DSX}, V_{GS} = - 5V			5	μA
	T_J = 125°C			100	μA
$R_{DS(on)}$	V_{GS} = 0V, I_D = 8A, Note 1			80	mΩ
$I_{D(on)}$	V_{GS} = 0V, V_{DS} = 25V, Note 1	16			A

Features

- Normally ON Mode
- International Standard Packages
- Molding Epoxies Meet UL 94 V-0 Flammability Classification

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Audio Amplifiers
- Start-up Circuits
- Protection Circuits
- Ramp Generators
- Current Regulators
- Active Loads

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Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.
g_{fs}	V_{DS} = 20V, I_D = 8A, Note 1	7	12	S
C_{iss}	V_{GS} = -10V, V_{DS} = 25V, f = 1MHz		5500	pF
C_{oss}			1360	pF
C_{rss}			607	pF
$t_{d(on)}$	**Resistive Switching Times**		46	ns
t_r	V_{GS} = ± 5V, V_{DS} = 100V, I_D = 8A		130	ns
$t_{d(off)}$	R_G = 3.3Ω (External)		270	ns
t_f			135	ns
$Q_{g(on)}$	V_{GS} = ± 5V, V_{DS} = 100V, I_D = 8A		208	nC
Q_{gs}			28	nC
Q_{gd}			110	nC
R_{thJC}				0.18 °C/W
R_{thCS}	TO-247		0.21	°C/W

Safe-Operating-Area Specification

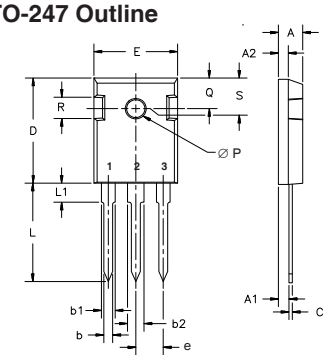
Symbol	Test Conditions	Characteristic Values Min.	Typ.	Max.
SOA	V_{DS} = 200V, I_D = 2.1A, T_C = 75°C, tp = 5s	420		W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.
V_{SD}	I_F = 16A, V_{GS} = -10V, Note 1		0.8	1.3 V
t_{rr}	I_F = 8A, -di/dt = 100A/μs		265	ns
I_{RM}	V_R = 100V, V_{GS} = -10V		14.3	A
Q_{RM}			1.9	μC

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

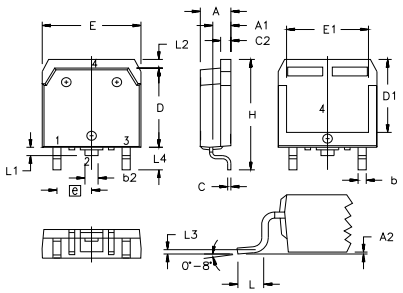
TO-247 Outline



Terminals: 1 - Gate 2 - Drain
3 - Source

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

TO-268 Outline



Terminals: 1 - Gate 2 - Drain
3 - Source 4 - Drain

SYM	INCHES MIN	MAX	MILLIMETERS MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25°C

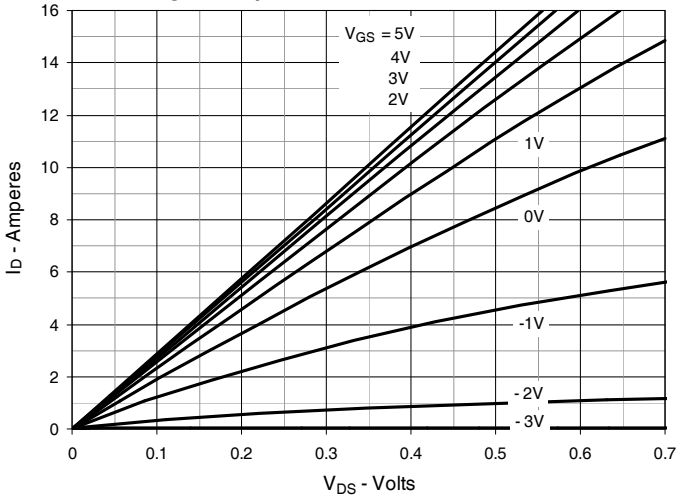


Fig. 2. Extended Output Characteristics @ T_J = 25°C

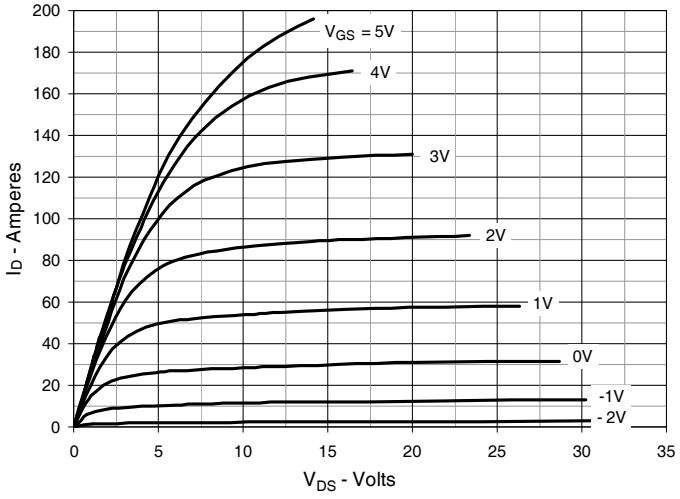


Fig. 3. Output Characteristics @ T_J = 125°C

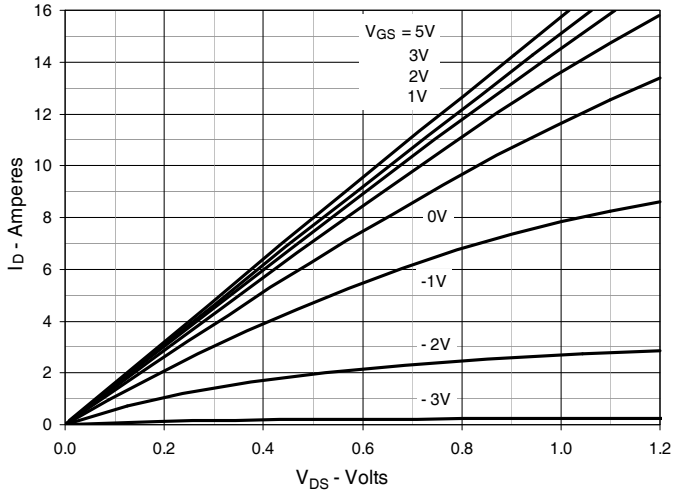


Fig. 4. Drain Current @ T_J = 25°C

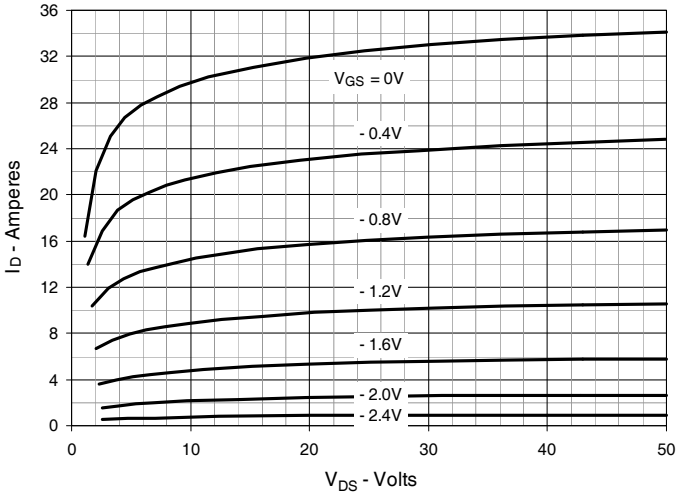


Fig. 5. Drain Current @ T_J = 100°C

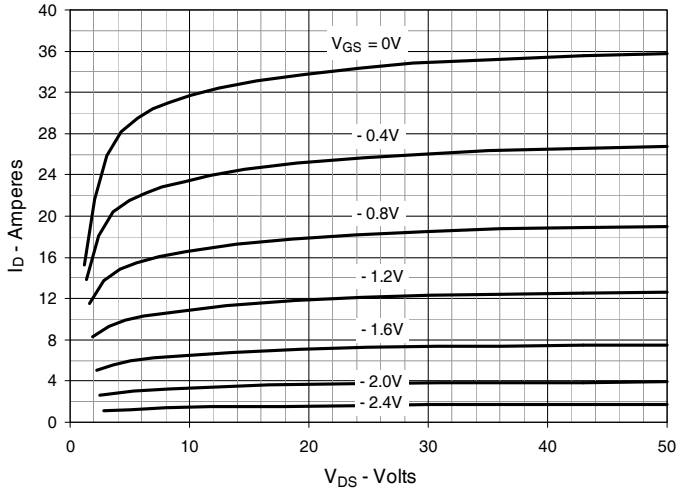
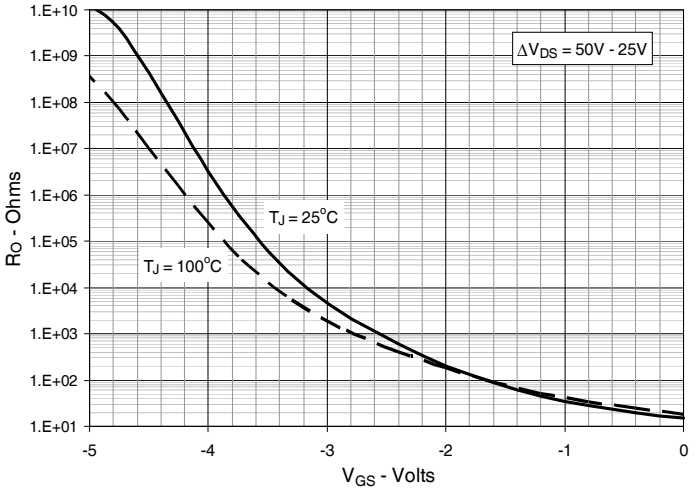


Fig. 6. Dynamic Resistance vs. Gate Voltage



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Fig. 7. Normalized $R_{DS(on)}$ vs. Junction Temperature

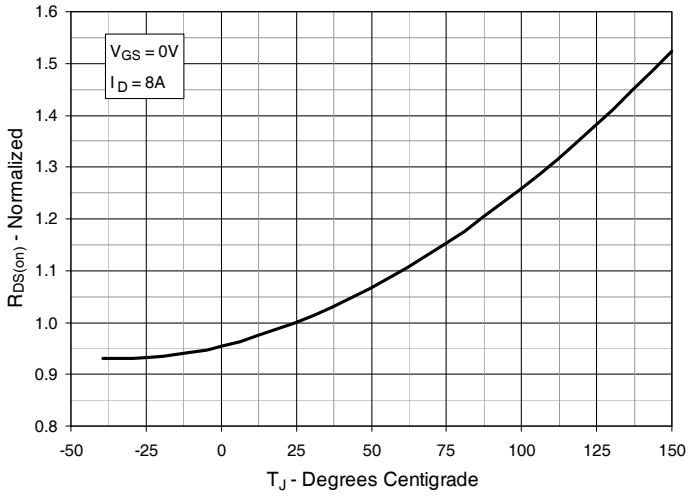


Fig. 8. $R_{DS(on)}$ Normalized to I_D = 8A Value vs. Drain Current

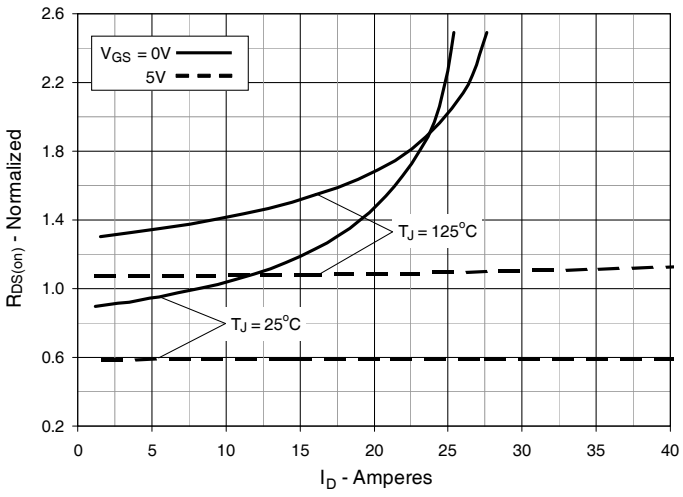


Fig. 9. Input Admittance

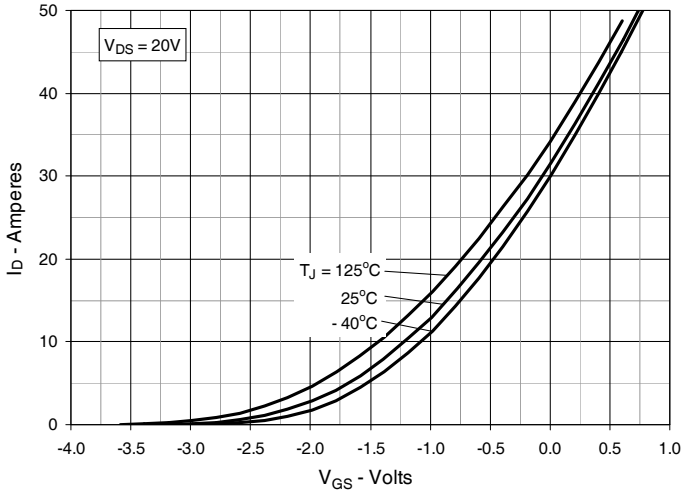


Fig. 10. Transconductance

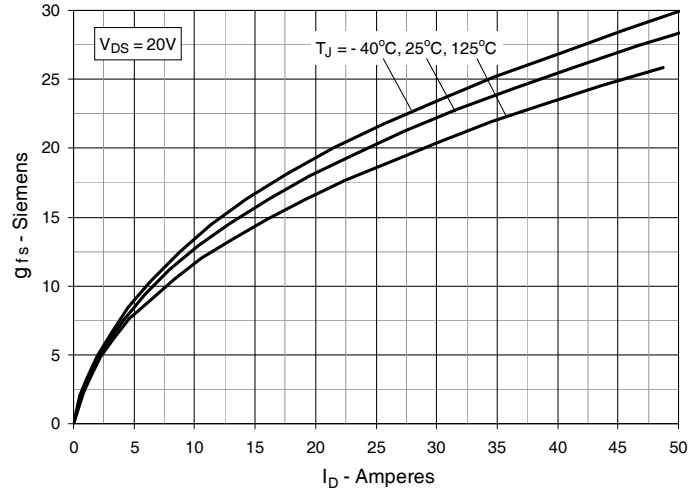


Fig. 11. Normalized Breakdown and Threshold Voltages vs. Junction Temperature

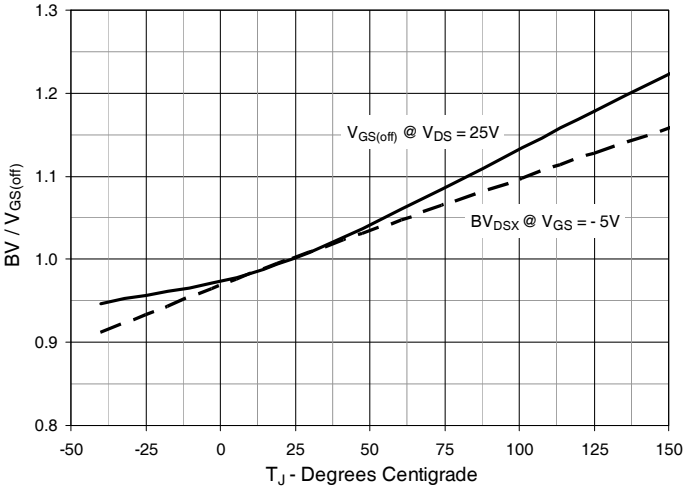
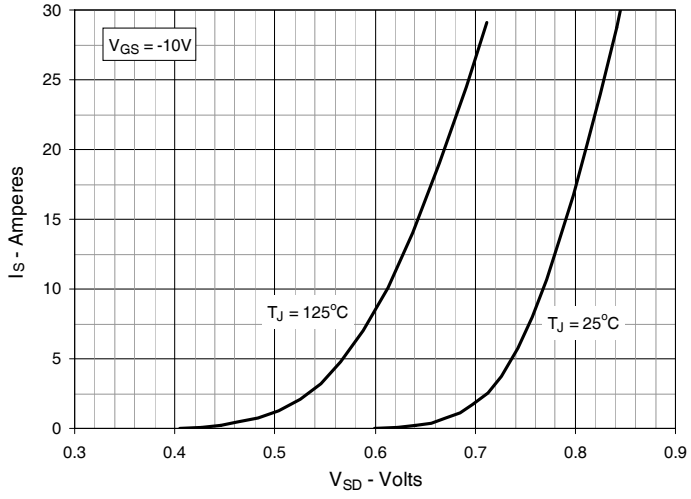


Fig. 12. Forward Voltage Drop of Intrinsic Diode



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Fig. 13. Capacitance

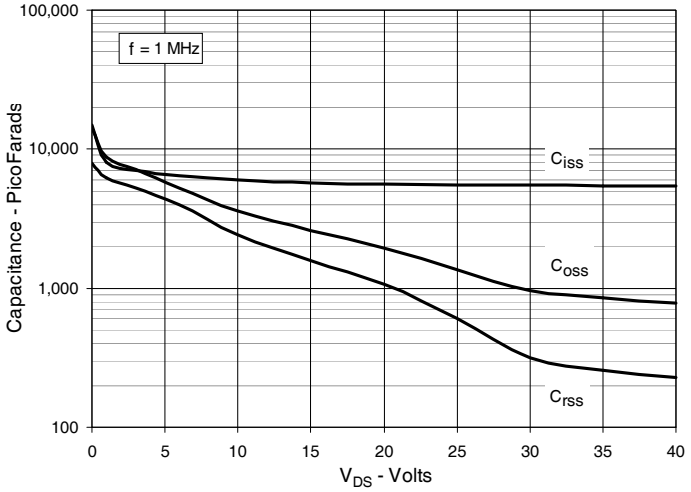


Fig. 14. Gate Charge

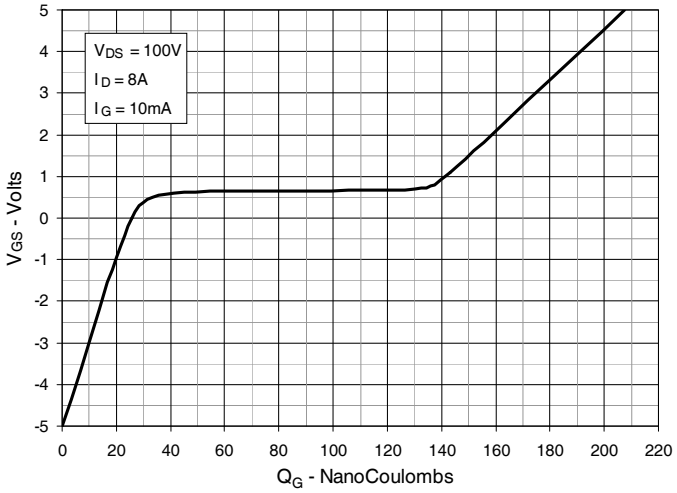


Fig. 15. Forward-Bias Safe Operating Area @ T_C = 25°C

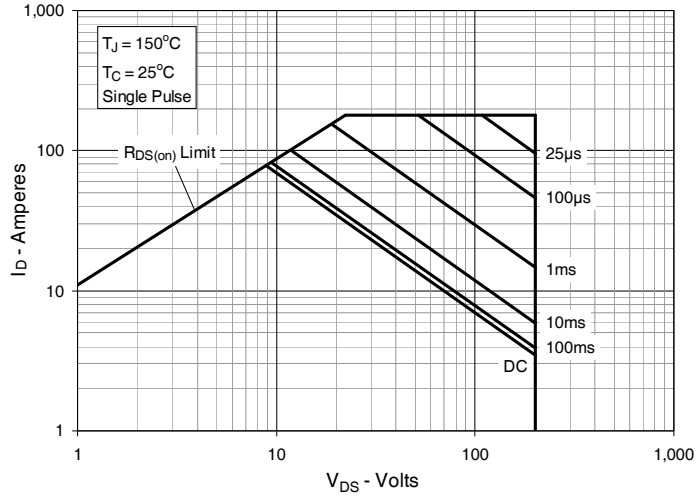


Fig. 16. Forward-Bias Safe Operating Area @ T_C = 75°C

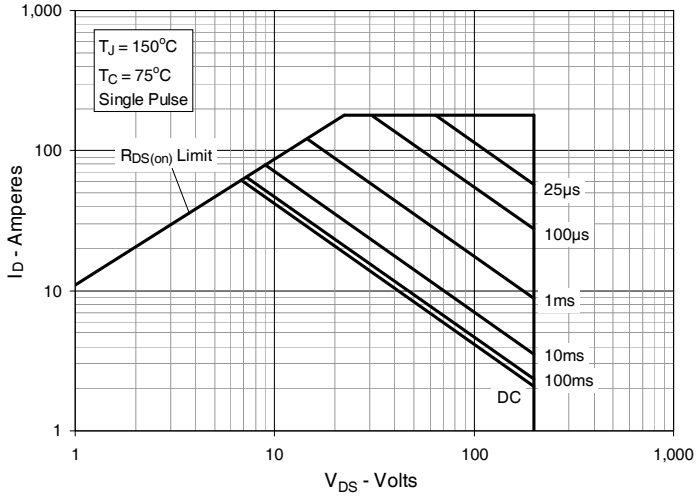
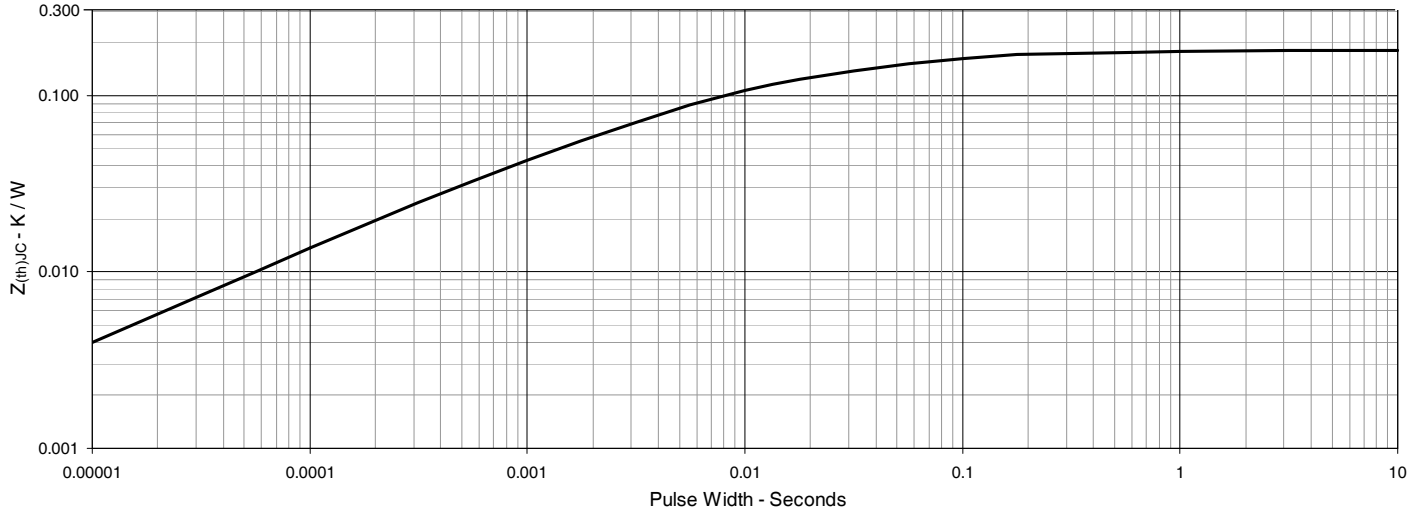


Fig. 17. Maximum Transient Thermal Impedance



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